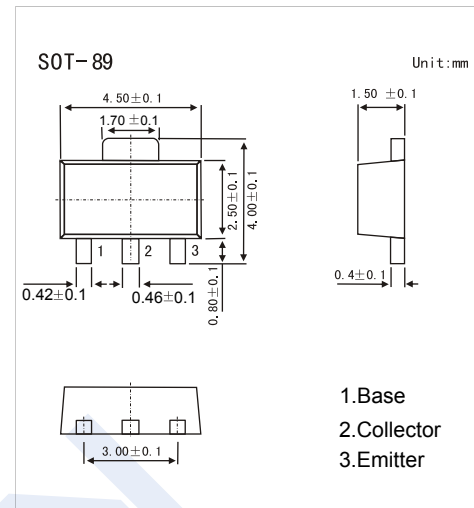


## PNP Transistors

### 2SA1364

#### ■ Features

- High Voltage  $V_{CE0} = -60V$
- High Collector Current ( $I_c = -1A$ )
- High Collector Dissipation  $P_c = 500mW$
- Small Package For Mounting
- Complementary to 2SC3444



#### ■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Collector-Base Voltage	$V_{CB0}$	-60	V
Collector-Emitter Voltage	$V_{CE0}$	-60	V
Emitter-Base Voltage	$V_{EB0}$	-6	V
Collector Current	$I_c$	-1	A
Peak Collector Current	$I_{CM}$	-2	A
Collector Power Dissipation	$P_c$	500	mW
Jumction temperature	$T_j$	150	$^\circ C$
Storage temperature Range	$T_{stg}$	-55 to +150	$^\circ C$

#### ■ Electrical Characteristics $T_a = 25^\circ C$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	$V_{CB0}$	$I_c = -100 \mu A, I_E = 0$	-60			V
Collector- emitter breakdown voltage	$V_{CE0}$	$I_c = -2 mA, I_B = 0$	-60			
Emitter - base breakdown voltage	$V_{EB0}$	$I_E = -100 \mu A, I_c = 0$	-6			nA
Collector-base cut-off current	$I_{CB0}$	$V_{CB} = -50 V, I_E = 0$			-200	
Emitter cut-off current	$I_{EB0}$	$V_{EB} = -4V, I_c = 0$			-200	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_c = -500mA, I_B = -25mA$		-0.11	-0.3	V
Base - emitter saturation voltage	$V_{BE(sat)}$	$I_c = -500mA, I_B = -25mA$			-1.2	
DC current gain	$h_{FE}$	$V_{CE} = -4V, I_c = -100mA$	55		300	
Collector output capacitance	$C_{ob}$	$V_{CB} = -10V, I_E = 0, f = 1MHz$		22		pF
Transition frequency	$f_T$	$V_{CE} = -2V, I_E = 10mA$		85		MHz

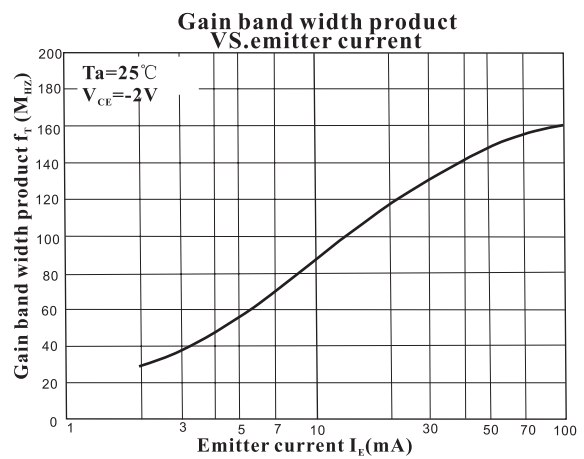
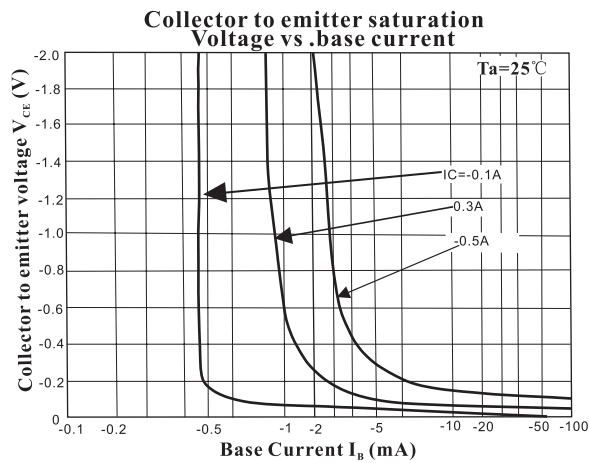
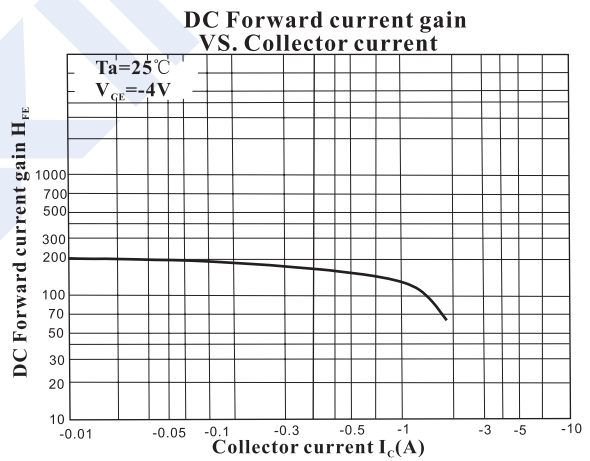
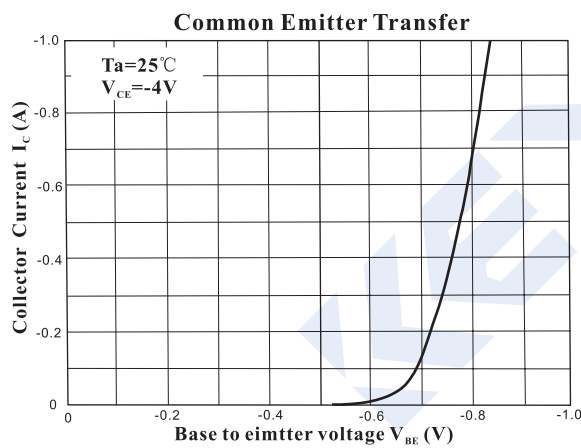
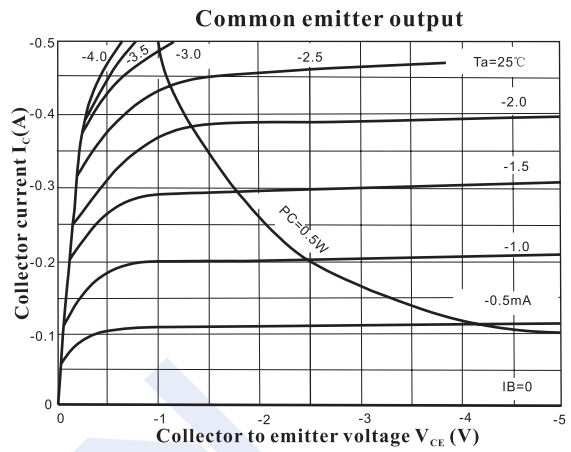
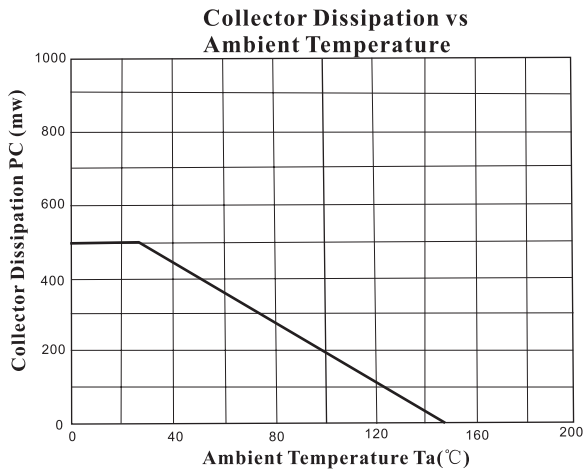
#### ■ Classification of $h_{FE}$

Type	2SA1364-C	2SA1364-D	2SA1364-E
Range	55-110	90-180	150-300
Marking	CC	CD	CE

# PNP Transistors

## 2SA1364

### Typical Characteristics



## PNP Transistors

### 2SA1364

#### ■ Typical Characteristics

